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Configurable Multifunction Gate

The NLX1G99 MiniGate^m is an advanced high-speed CMOS multifunction gate with a 3-state output. With the output enable input (\overline{OE}) at High, the output is disabled and is kept at high impedance. With the output enable input (\overline{OE}) at Low, the device can be configured for logic functions such as MUX, AND, OR, NAND, NOR, XOR, XNOR, INVERT and BUFFER, depending on the combination of the 4-bit input. The device has Schmitt-trigger inputs, thereby enhancing noise immunity.

The NLX1G99 input and output structures provide protection when voltages up to 7.0 V are applied, regardless of the supply voltage.

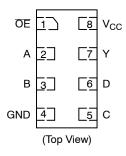
Features

- High Speed: $t_{PD} = 6.7 \text{ ns} (Max) @ V_{CC} = 3.3 \text{ V}$
- Low Power Dissipation: $I_{CC} = 1 \mu A$ (Max) at $T_A = 25^{\circ}C$
- Power Down Protection Provided on inputs
- Balanced Propagation Delays
- Overvoltage Tolerant (OVT) Input and Output Pins
- Ultra-Small Packages
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

PIN ASSIGNMENT

1	ŌĒ
2	А
3	В
4	GND
5	С
6	D
7	Y
8	V _{CC}

PIN ASSIGNMENTS





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	MARKING DIAGRAMS
UDFN8 1.45 x 1.0 CASE 517BZ	1 o
UDFN8 1.6 x 1.0 CASE 517BY	1 • X M
UDFN8 1.95 x 1.0 CASE 517CA	AF M 1 •

AA or E = Specific Device Code M = Date Code

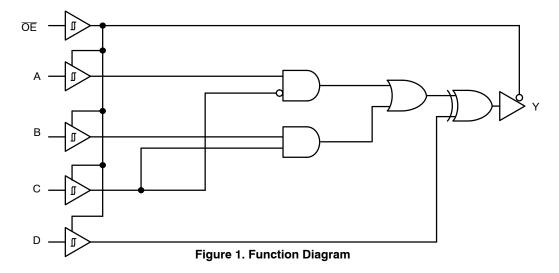
= Date Code = Pb-Free Package

= PD-Flee Fackage

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

FUNCTION DIAGRAM



FUNCTION TABLE*

	INPUT								
OE	D	С	В	А	Y				
L	L	L	L	L	L				
L	L	L	L	н	н				
L	L	L	н	L	L				
L	L	L	н	н	н				
L	L	Н	L	L	L				
L	L	н	L	н	L				
L	L	Н	Н	L	н				
L	L	Н	н	н	н				
L	Н	L	L	L	Н				
L	н	L	L	н	L				
L	н	L	Н	L	н				
L	н	L	н	н	L				
L	Н	Н	L	L	Н				
L	н	н	L	н	н				
L	н	Н	н	L	L				
L	н	н	н	н	L				
Н	H or L	H or L	H or L	H or L	Z				

*To select a logic function, please refer to "Logic Configurations" section.

FUNCTION SELECTION	LOGIC CONFIGURATION PAGE
3-State Buffers	3
3-State Inverters	3
3-State MUXes	3
3-State AND / OR / NOR	4
3-State NAND / OR	5
3-State XOR/XNOR	6

LOGIC CONFIGURATIONS

3-State Buffer Functions Available

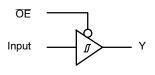
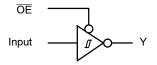


Figure 2.

Function	OE	А	В	С	D
3-State Buffer	L	Input H or L L H H H or L L	H or L Input H L H or L L L	L H Input Input L H H or L	L L H Input Input Input

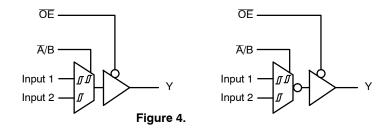
3-State Inverter Functions Available





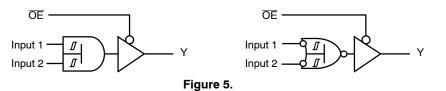
Function	ŌĒ	А	В	С	D
3-State Buffer	L	Input X L H H or L H	H or L Input H L H or L H H	L H Input Input L H H or L	H H L Input Input Input

3-State MUX Functions Available

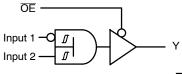


Function	OE	Α	В	С	D
3-State 2-to-1	L	Input 1	Input 2	Input 1 or Input 2	L
3-State 2-to-1		Input 2	Input 1	Input 2 or Input 1	L
3-State 2-to-1, Inverted Out		Input 1	Input 2	Input 1 or Input 2	H
3-State 2-to-1, Inverted Out		Input 2	Input 1	Input 2 or Input 1	H

3-State AND/NOR/OR Function Available



No. of Inputs	AND/NAND Function	OR/NOR Function	ŌE	А	В	С	D
2 2	3–State AND 3–State AND	3–State NOR 3–State NOR	L	L	Input 1 Input 2	Input 2 Input 1	L L



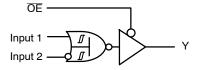
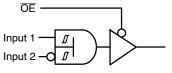


Figure 6.

No. of Inputs	AND/NAND Function	OR/NOR Function	ŌĒ	Α	В	С	D
2	3-State AND	3–State NOR	L	Input 2	L	Input 1	L
2	3-State AND	3–State NOR		H	Input 1	Input 2	H



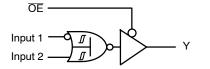
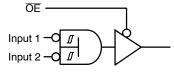
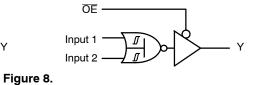


Figure 7.

No. of Inputs	AND/NAND Function	OR/NOR Function	ŌE	Α	В	С	D
2	3–State AND	3-State NOR	L	Input 1	L	Input 2	L
2	3–State AND	3-State NOR		H	Input 2	Input 1	H





Input 2

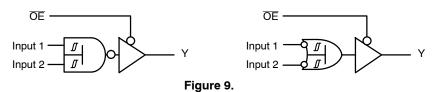
Н

Input 1

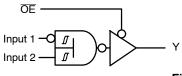
AND/NAND Function OR/NOR Function No. of Inputs OE Α в С D 3-State AND 3-State AND 3-State NOR 3-State NOR 2 2 L Input 1 Н Input 2 Н Н

Υ

3-State NAND/OR Function Available



No. of Inputs	AND/NAND Function	OR/NOR Function	ŌE	Α	В	С	D
2 2	3-State NAND 3-State NAND	3–State OR 3–State OR	L	L	Input 1 Input 2	Input 2 Input 1	H H



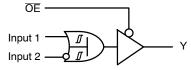
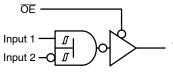


Figure 10.

No. of Inputs	AND/NAND Function	OR/NOR Function	ŌE	Α	В	С	D
2 2	3–State NAND 3–State NAND	3–State OR 3–State OR	L	Input 2 H	L Input 1	Input 1 Input 2	H L



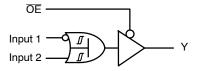
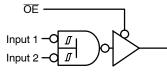


Figure 11.

No. of Inputs	AND/NAND Function	OR/NOR Function	ŌE	Α	В	С	D
2	3-State NAND	3–State OR	L	Input 1	L	Input 2	H
2	3-State NAND	3–State OR		H	Input 2	Input 1	L



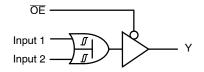


Figure 12.

No. of Inputs	AND/NAND Function	OR/NOR Function	ŌĒ	Α	В	С	D
2 2	3-State AND 3-State AND	3–State OR 3–State OR	L	Input 1 Input 2	ΗH	Input 2 Input 1	L

3-State XOR/XNOR Function Available

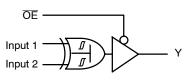
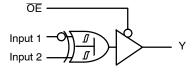


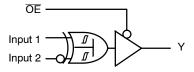
Figure 13.

Function	ŌĒ	А	В	С	D
3–State XOR	L	Input 1 Input 2 H or L H or L L L	H or L H or L Input 1 Input 2 H H	L L H Input 1 Input 2	Input 2 Input 1 Input 2 Input 1 Input 2 Input 1





Function	ŌĒ	А	В	С	D
3–State XOR	L	Н	L	Input 1	Input 2





Function	ŌE	А	В	С	D
3–State XOR	L	Н	L	Input 1	Input 2

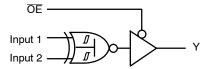


Figure 16.

Function	ŌĒ	А	В	С	D
3–State XNOR 3–State XNOR	L	НН	L	Input 1 Input 2	Input 2 Input 1

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V
V _{IN}	DC Input Voltage	-0.5 to +7.0	V
V _{OUT}	DC Output Voltage Active Mode (High or Low State) Tristate Mode (Output at Hi–Z) Power Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +7.0 -0.5 to +7.0	V
I _{IK}	DC Input Diode Current V _{IN} < GND	-50	mA
I _{OK}	DC Output Diode Current V _{OUT} < GND	-50	mA
Ι _Ο	DC Output Source/Sink Current	±50	mA
I _{CC}	DC Supply Current Per Supply Pin	±100	mA
I _{GND}	DC Ground Current per Ground Pin	±100	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C
ΤL	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias	150	°C
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 N/A	V
ILATCHUP	Latchup Performance Above V _{CC} and Below GND at 125°C (Note 5)	±500	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.

Tested to EIA / JESD22–A114–A.
Tested to EIA / JESD22–A115–A.

4. Tested to JESD22–C101–A.

5. Tested to EIA / JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Para	ameter	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage		1.65	5.5	V
V _{IN}	Digital Input Voltage		0	5.5	V
V _{OUT}	Output Voltage	Active Mode (High or Low State) Tristate Mode (Output at Hi-Z) Power Down Mode (V _{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	V
T _A	Operating Free-Air Temperature		-55	+125	°C
Δt /ΔV	Input Transition Rise or Fall Rate	$\begin{array}{l} V_{CC} = 2.5 \ V \ \pm \ 0.2 \ V \\ V_{CC} = 3.3 \ V \ \pm \ 0.3 \ V \\ V_{CC} = 5.0 \ V \ \pm \ 0.5 \ V \end{array}$	0 0 0	No Limit No Limit No Limit	nS/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

				T _A = 2	5°C	T _A ≤ +8	85°C	T _A = -55 +125		
Symbol	Parameter	Conditions	V _{CC} (V)	Min	Max	Min	Max	Min	Max	Unit
V _{T+}	Positive Threshold Voltage		1.65 1.8 2.3 3.0 4.5 5.5	0.79 0.87 1.11 1.5 2.16 2.61	1.16 1.28 1.56 1.87 2.74 3.33		1.16 1.28 1.56 1.87 2.74 3.33		1.16 1.28 1.56 1.87 2.74 3.33	V
V _{T-}	Negative Threshold Voltage		1.65 1.8 2.3 3.0 4.5 5.5	0.35 0.38 0.58 0.84 1.41 1.78	0.62 0.68 0.87 1.19 1.9 2.29	0.35 0.38 0.58 0.84 1.41 1.78		0.35 0.38 0.58 0.84 1.41 1.78		V
V _H	Hysteresis Voltage		1.65 1.8 2.3 3.0 4.5 5.5	0.30 0.33 0.40 0.53 0.71 0.8	0.62 0.68 0.8 0.87 1.04 1.2	0.30 0.33 0.40 0.53 0.71 0.8	0.62 0.68 0.8 0.87 1.04 1.2	0.30 0.33 0.40 0.53 0.71 0.8	0.62 0.68 0.8 0.87 1.04 1.2	V
V _{OH}	Minimum High-Level Output Voltage	$\begin{array}{l} V_{IN} = V_{T-MIN} \text{ or } \\ V_{T+MAX} \\ I_{OH} = -50 \ \mu\text{A} \\ I_{OH} = -100 \ \mu\text{A} \end{array}$	1.65–5.5 1.65–5.5	V _{CC} -0.1 V _{CC} -0.1		V _{CC} -0.1 V _{CC} -0.1		V _{CC} -0.1 V _{CC} -0.1		V
		$\begin{array}{c} V_{IN} = V_{T-MIN} \ or \\ V_{T+MAX} \\ I_{OH} = -4 \ mA \\ I_{OH} = -8 \ mA \\ I_{OH} = -12 \ mA \\ I_{OH} = -16 \ mA \\ I_{OH} = -24 \ mA \\ I_{OH} = -32 \ mA \end{array}$	1.65 2.3 2.7 3.0 3.0 4.5	1.2 1.9 2.2 2.4 2.3 3.8		1.2 1.9 2.2 2.4 2.3 3.8		1.2 1.9 2.2 2.4 2.3 3.8		V
V _{OL}	Maximum Low-Level Output Voltage	$V_{IN} = V_{T-MIN} \text{ or } \\ V_{T+MAX} \\ I_{OL} = 50 \ \mu\text{A} \\ I_{OL} = 100 \ \mu\text{A} \\ \end{cases}$	1.65–5.5 1.65–5.5		0.1 0.1		0.1 0.1		0.1 0.1	V
		$V_{IN} = V_{T-MIN} \text{ or } \\ V_{T+MAX} \\ I_{OL} = 4 \text{ mA} \\ I_{OL} = 8 \text{ mA} \\ I_{OL} = 12 \text{ mA} \\ I_{OL} = 16 \text{ mA} \\ I_{OL} = 24 \text{ mA} \\ I_{OL} = 32 \text{ mA} \\ \end{cases}$	1.65 2.3 2.7 3.0 3.0 4.5		0.45 0.3 0.4 0.4 0.55 0.55		0.45 0.3 0.4 0.4 0.55 0.55		0.45 0.3 0.4 0.4 0.55 0.55	
I _{IN}	Input Leakage Current	$0 \le V_{IN} \le 5.5 V$	0 – 5.5		±0.1		±1.0		±1.0	μΑ
I _{off}	Power off Leakage Current	V _{IN} or V _O = 5.5 V	0		±1.0		±10		±10	μΑ
I _{OZ}	Tri–state Output Leakage Current	V _O = V _{CC} or GND	1.65–5.5		±1.0		±10		±10	μA
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND, I _O = 0	1.65–5.5		1.0		10		10	μΑ
ΔI _{CC}	Increase in I _{CC} Per Input	One input at $(V_{CC}$ –0.6) V, other inputs at V_{CC} or GND	2.3 – 5.5		10		100		100	μΑ

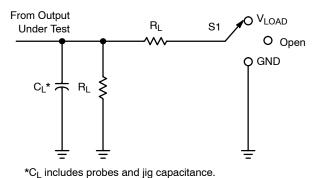
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

				1	(_A = 25°		T _A ≤	+85°C	T _A = - to +1	-55°C 25°C	
Symbol	Parameter	V _{CC} (V)	Test Condition	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Propagation Delay, Any Input to Output Y (See Test Circuit)	1.65-1.95 2.3 - 2.7 3.0 - 3.6 4.5 - 5.5	Refer to switch positions and loading conditions in Figure 17 to 21.	4.3 2.4 1.7 1.3	12.8 7.1 5.2 4.0	25.1 10.2 6.7 4.5	4.3 2.4 1.7 1.3	25.1 10.2 6.9 4.9	4.3 2.4 1.7 1.3	25.1 10.2 7.0 5.0	ns
t _{EN}	Output Enable Time, OE to Y	1.65–1.95 2.3 – 2.7 3.0 – 3.6 4.5 – 5.5	Refer to switch positions and loading conditions in Figure 17 to 21.	3.4 2.1 1.3 1.0		24.7 11 7.5 5.7	3.4 2.1 1.3 1.0	24.7 12 8.0 6.2	3.4 2.1 1.3 1.0	24.7 12.2 8.3 6.5	ns
t _{DIS}	Output Disable Time, OE to Y	1.65–1.95 2.3 – 2.7 3.0 – 3.6 4.5 – 5.5	Refer to switch positions and loading conditions in Figure 17 to 21.	4.0 2.7 3.5 2.0		15.5 7.5 7.0 5.5	4.0 2.7 3.5 2.0	15.5 7.5 7.0 5.5	4.0 2.7 3.5 2.0	15.5 7.5 7.0 5.5	ns
t _{PLH} , t _{PHL}	Propagation Delay, Any Input to Output Y (See Test Circuit)	1.65–1.95 2.3 – 2.7 3.0 – 3.6 4.5 – 5.5	Refer to switch Positions and loading conditions in Figure 22 to 26.	4.3 2.5 2.3 1.6	13.6 7.8 5.6 4.4	25.7 10.7 7.6 5.2	4.3 2.5 2.3 1.6	25.7 10.7 7.6 5.2	4.3 2.5 2.3 1.6	25.7 ns 10.7 7.6 5.2	
t _{EN}	Output Enable Time, OE to Y	1.65–1.95 2.3 – 2.7 3.0 – 3.6 4.5 – 5.5	Refer to switch Positions and loading conditions in Figure 22 to 26.	4.2 2.4 2.0 1.7		25.2 11.3 8.0 6.0	4.2 2.4 2.0 1.7	25.2 12.2 8.5 6.5	4.2 2.4 2.0 1.7	25.2 13 8.7 6.7	ns
t _{DIS}	Output Disable Time, OE to Y	1.65–1.95 2.3 – 2.7 3.0 – 3.6 4.5 – 5.5	Refer to switch Positions and loading conditions in Figure 22 to 26.	3.7 2.0 2.1 1.0		15 6.5 5.6 4.5	3.7 2.0 2.1 1.0	15 6.7 5.8 4.7	3.7 2.0 2.1 1.0	15 6.9 5.9 4.9	ns
C _{IN}	Input Capacitance	3.3			3.5						pF
C _O	Output Capacitance	3.3			6.0						pF
C _{PD}	Power Dissipation Capacitance (Note 6)	3.3	f = 10 MHz		22						pF

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no-load dynamic power consumption: P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

TEST CIRCUIT AND VOLTAGE WAVEFORMS



Test	S1			
t _{PLH} /t _{PHL}	Open			
t _{PLZ} /t _{PZL}	V _{LOAD}			
t _{PHZ} /t _{PZH}	GND			

Figure 17. Load Circuit

	Inputs						
V _{cc}	VI	t _r /t _f	VM	V_{LOAD}	CL	RL	V_{Δ}
$1.8~V~\pm~0.15~V$	V _{CC}	$\leq 2 \text{ ns}$	V _{CC} /2	$2 \times V_{CC}$	15 pF	1 MΩ	0.15 V
$2.5~V~\pm~0.2~V$	V _{CC}	$\leq 2 \text{ ns}$	V _{CC} /2	$2 \times V_{CC}$	15 pF	1 MΩ	0.15 V
3.3 V \pm 0.3 V	3 V	\leq 2.5 ns	1.5 V	6 V	15 pF	1 MΩ	0.3 V
5.5 V \pm 0.5 V	V _{CC}	\leq 2.5 ns	V _{CC} /2	$2 \times V_{CC}$	15 pF	1 MΩ	0.3 V

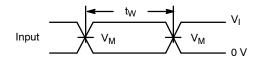


Figure 18. Voltage Waveforms Pulse Duration

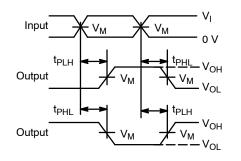


Figure 20. Voltage Waveforms Propagation Delay Times Inverting and Noninverting Outputs

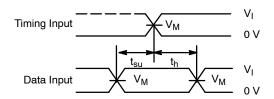


Figure 19. Voltage Waveforms Setup and Hold Times

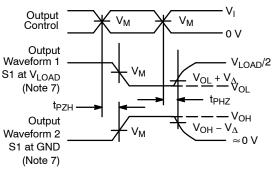
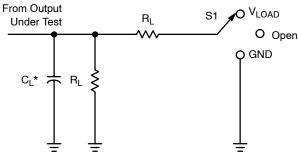


Figure 21. Voltage Waveforms Enable and Disable Times Low- and High-Level Enabling

 Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control
All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω.

9. The outputs are measured one at a time, with one transition per measurement.

10. All parameters are waveforms are not applicable to all devices.



Test	S1
t _{PLH} /t _{PHL}	Open
t _{PLZ} /t _{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

*C_L includes probes and jig capacitance.

Figure 22. Load Circuit

	Inputs						
V _{cc}	VI	t _r /t _f	VM	V_{LOAD}	CL	RL	ν _Δ
$1.8 \text{ V} \pm 0.15 \text{ V}$	V _{CC}	$\leq 2 \text{ ns}$	V _{CC} /2	$2 \times V_{CC}$	30 pF	1 kΩ	0.15 V
$2.5~V~\pm~0.2~V$	V _{CC}	$\leq 2 \text{ ns}$	V _{CC} /2	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V
$3.3~V~\pm~0.3~V$	3 V	\leq 2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5.5 V \pm 0.5 V	V _{CC}	\leq 2.5 ns	V _{CC} /2	$2 \times V_{CC}$	50 pF	500 Ω	0.3 V

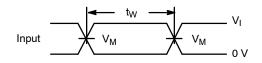


Figure 23. Voltage Waveforms Pulse Duration

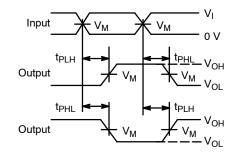


Figure 25. Voltage Waveforms Propagation Delay Times Inverting and Noninverting Outputs

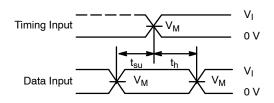


Figure 24. Voltage Waveforms Setup and Hold Times

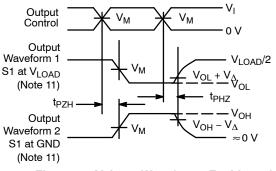


Figure 26. Voltage Waveforms Enable and Disable Times Low- and High-Level Enabling

11. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control

12. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω . 13. The outputs are measured one at a time, with one transition per measurement.

14. All parameters are waveforms are not applicable to all devices.

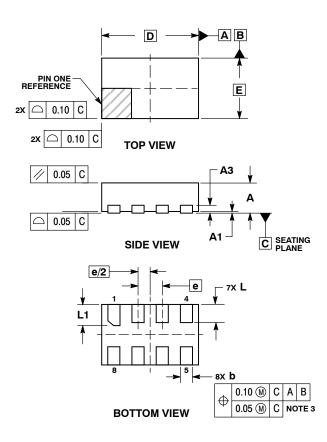
ORDERING INFORMATION

Device	Package	Shipping [†]		
NLX1G99DMUTCG	UDFN8, 1.95 x 1.0, 0.5P (Pb-Free)	3000 / Tape & Reel		
NLX1G99DMUTWG	UDFN8, 1.95 x 1.0, 0.5P (Pb-Free)	3000 / Tape & Reel		
NLX1G99EMUTCG (In Development)	UDFN8, 1.6 x 1.0, 0.4P (Pb-Free)	3000 / Tape & Reel		
NLX1G99FMUTCG (In Development)	UDFN8, 1.45 x 1.0, 0.35P (Pb–Free)	3000 / Tape & Reel		

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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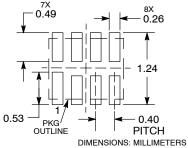
UDFN8 1.6x1.0, 0.4P CASE 517BY ISSUE O



NOTES:
DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
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DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45	0.55	
A1	0.00	0.05	
A3	0.13 REF		
b	0.15	0.25	
D	1.60 BSC 1.00 BSC		
Е			
е	0.40 BSC		
L	0.25	0.35	
L1	0.30	0.40	

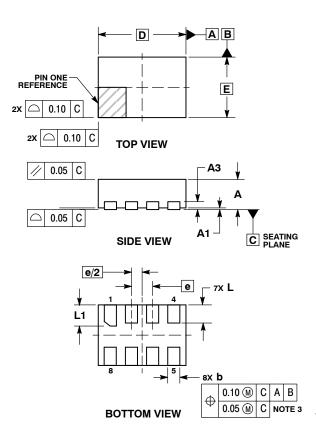
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*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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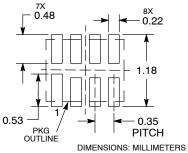
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	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45	0.55	
A1	0.00	0.05	
A3	0.13 REF		
b	0.15	0.25	
D	1.45 BSC 1.00 BSC		
Е			
е	0.35 BSC		
Ĺ	0.25	0.35	
L1	0.30	0.40	

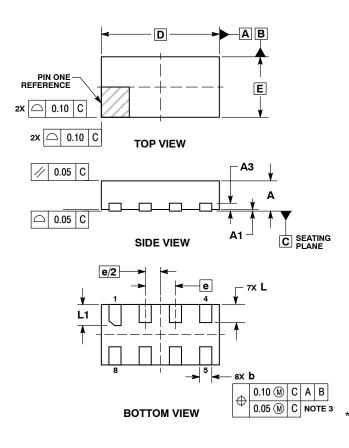
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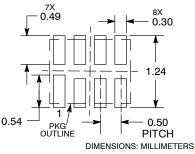
UDFN8 1.95x1.0, 0.5P CASE 517CA **ISSUE O**



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- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN З.
- 0.15 AND 0.20 MM FROM TERMINAL TIP. PACKAGE DIMENSIONS EXCLUSIVE OF 4
- BURRS AND MOLD FLASH.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45	0.55	
A1	0.00	0.05	
A3	0.13 REF		
b	0.15	0.25	
D	1.95	BSC	
Е	1.00 BSC 0.50 BSC		
е			
L	0.25	0.35	
L1	0.30	0.40	

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